

What is Claimed Is:

Sub A1

1. A semiconductor pressure sensor comprising;
a substrate,
5 a diaphragm formed on said substrate by
sacrificial layer etching method, and
a silicon oxide film provided by sealing the
etchant filling hole of the sacrificial layer on the
said diaphragm;

10 said semiconductor pressure sensor characterized
in that a polysilicon film is provided to cover part
or whole of said silicon oxide film.

2. A semiconductor pressure sensor according to
15 Claim 1 characterized in that the distance of said
covered part is at least 10 microns or less from said
etchant filling hole.

3. A semiconductor pressure sensor according to
20 Claim 1 characterized in that the thickness of said
polysilicon film is 0.1 microns or more.

4. A semiconductor pressure sensor according to
Claim 1 characterized in that the thickness of said
25 polysilicon film is 0.1 microns and over up to and

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including 0.4 microns.

5. A pressure detector comprising;

(a) a detector further comprising as an integral
5 unit;

a substrate,

a diaphragm formed on said substrate by
sacrificial layer etching method,

a silicon oxide film provided by sealing the
10 etchant filling hole of the sacrificial layer on the
said diaphragm, and

a polysilicon film covering part or whole of said
silicon oxide film;

(b) a correction circuit for correction of the
15 output of said detector;

(d) a package enclosing said correction circuit
and said detector; and

(d) an intake tube provided in said package and
used for introduction of external pressure to said
20 detector.

6. A pressure detector according to Claim 5
characterized in that (h) the distance of said covered
part is at least 10 microns or less from said etchant
25 filling hole.

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7. A pressure detector according to Claim 5 characterized in that (i) the thickness of said polysilicon film is 0.1 microns or more.

5 8. A pressure detector according to Claim 5 characterized in that (j) the thickness of said polysilicon film is 0.1 microns and over up to and including 0.4 microns.

10 9. A pressure detector according to Claim 5 comprising;

(e) a sub-package further comprising said correction circuit and said detector as an integral unit, and having on the surface a pad connected to
15 said correction circuit, and

(f) an output terminal removably connected to the external signal line and used to send a signal from said correction circuit to the external signal line;

said pressure detector further characterized in
20 that

(g) said correction circuit and said detector are enclosed by said package after said pad and said output terminal are connected by a metal wire.

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